Supporting information to

## Band Gap Opening and Semiconductor-metal Phase Transition in (n, n) Single-Walled Carbon Nanotubes with Distinctive Boron-Nitrogen Line Defect

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Fig. S1. The band structures of decorated ZGNRs with different widths 4, 8, 12 and 16.



Fig. S2. The evolution of formation energy with different widths from 4 to 24.



Fig. S3. The electron density of (a) 4bn@CNT, (b) 8bn@CNT, (c) 12bn@CNT and and (d) 16bn@CNT.



Fig. S4. The increasement of B–N bond on the bn@CNTs with the widths 4 to 24.



Fig. S5. The projected density of states of (a) 4bn@CNT, (b) 8bn@CNT, (c) 12bn@CNT, and (d) 16bn@CNT. TDOS is the total density of states. B (N) is the Projected density of states on the B (N) atom.



Fig. S6. The evolution of dipole moments of 4bn@CNT and 12bn@CNT along the y axis under uniaxial compressive deformation.



Fig. S7. The evolution of frontier orbitals HOMO and LUMO of different bn@CNTs under uniaxial compressive deformation.



Fig. S8. The projected density of states of (a) 4bn@CNT and (b) 12bn@CNT under uniaxial compressive deformation. TDOS is the total density of states. B (N) is the Projected density of states on the B (N) atom.



Fig. S9. The ratios,  $R = G_{Electric field}/G_0$ , of different bn@CNTs under the electric field applied along the x axis. The  $G_{Electric field}$  is the band gap under the applied electric field and  $G_0$  is the band gap without applied electric field.



Fig. S10. The eigenstates HOMO and LUMO of the 16bn@CNT at the applied electric fields of 0,  $\pm 0.01$  and  $\pm 0.10V/Å$ .